

**SCHOTTKY DIE SPECIFICATION**

TYPE: MBR16100

General Description: 100 V 15 A (Low Ir)

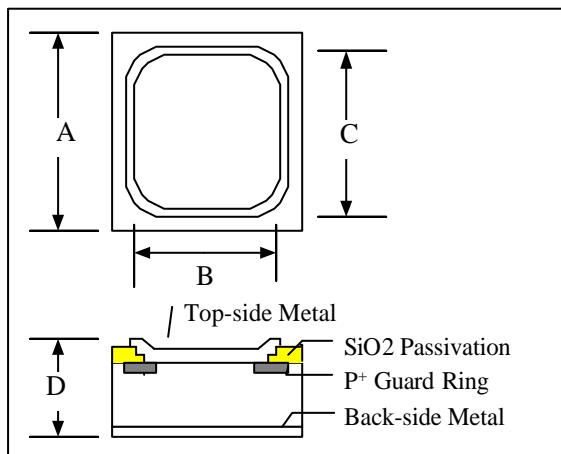
Single Anode

<b>ELECTRICAL CHARACTERISTICS</b>	<b>SYM</b>	<b>Spec. Limit</b>	<b>Die Sort</b>	<b>UNIT</b>
DC Blocking Voltage: Ir=1mA(for wafer form)	VRRM	100	105	Volt
Ir=0.5mA (for dice form)				
Average Rectified Forward Current	IFAV	15		Amp
Maximum Instantaneous Forward Voltage				
@ 15 Amperes, Ta=25°C	VF MAX	0.82	0.81	Volt
@ 8 Amperes, 25°C		0.72	0.71	
Maximum Instantaneous Reverse Voltage				
VR= 100 Volt, Ta=25°C	IR MAX	0.2	0.18	mA
Maximum Junction Capacitance @ 0V, 1MHZ	Cj MAX			pF
<b>MAXIMUM RATINGS</b>				
Nonrepetitive Peak Surge Current	IFSM	250		Amp
Operating Junction Temperature	Tj	-65 to +125		°C
Storage Temperatures	TSTG	-65 to +125		°C

Specification apply to die only. Actual performance may degrade when assembled.

MEMT does not guarantee device performance after assembly.

Data sheet information is subjected to change without notice.

**DICE OUTLINE DRAWING**


<b>DIM</b>	<b>ITEM</b>	<b>um<sup>2</sup></b>	<b>Mil<sup>2</sup></b>
A	Die Size	3116	122.67
B	Top Metal Pad Size	3016	118.7
C	Passivation Seal	3036	119.5
D	Thickness (Min)	254	10
	Thickness (Max)	305	12

**PS:**

(1)Cutting street width is around 80um(3.14mil).

(2)Both of top-side and back-side metals are Ti/Ni/Ag.